
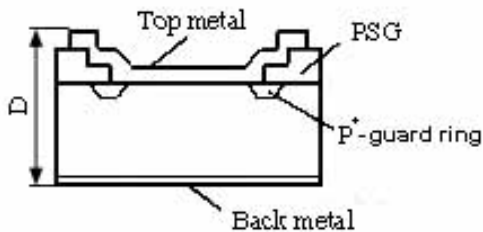
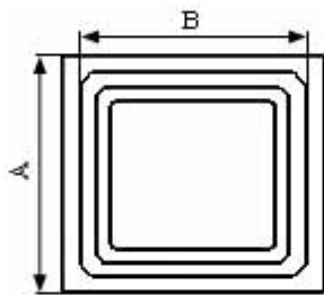


# SCHOTTKY DIODES KDN-01060.



Rev.1. Feb. 2010

 <b>VSP-MIKRON</b>		<b>1A/60V. Die Size-32mil.</b>		
<b>Electrical Characteristics</b>	<b>Symbol</b>	<b>Unit</b>	<b>Spec. limit</b>	<b>Die Sort</b>
Breakdown Voltage @ $I_R=10mA$	$V_{BR}$	V	60	65
Average Rectified Forward Current	$I_{F(AV)}$	A	1,0	-
DC Forward Voltage @ 25°C, $I_F=1,0A$	$V_F$	V	0,70	0,68
Maximum Reverse Current @ 25°C, $V_R=65V$ 25°C, $V_R=60V$ 125°C, $V_R=60V$	$I_R$	mA	- 0,040 10,0	0,040 0,030 9,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	20	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<150°C$ .	$I_{RRM}$	A	1,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	150	



<b>DIM</b>	<b>ITEM</b>	<b>µm</b>
$A_x$ $A_y$	Wafer Form Die Size	810 810
$B_x$ $B_y$	Top Metal Size	670 670
D	Thickness	300max.
Scribe line Width		80

*Top metal:* a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag** – for Soldering.

*Backside metal:* **Ti-Ni-Ag**.